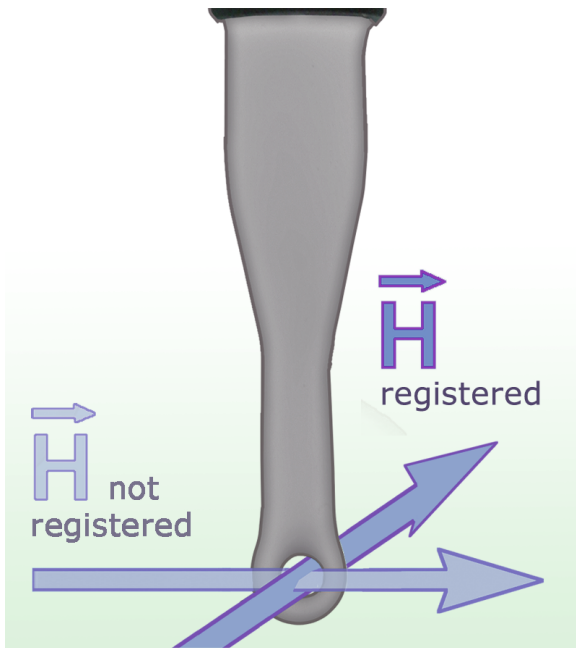


# XF-R 3-1

H-Field Probe 30 MHz up to 6 GHz



## Short description

The XF-R 3-1 near-field probe is designed for direct high-resolution measurements of RF magnetic fields on an assembly, e.g. around the pins and IC cases, conducting paths, decoupling capacitor, and EMC components.

In principle the XF-R 3-1 H-field probe has the same structure as the XF-R 100-1 and XF-R 400-1 probes. The resolution of the XF-R 3-1 is significantly higher. The H-field probe is suitable for measurements close to the components with high magnetic field strength. It is not suitable for measurements from large distances, which can be done using XF-R 400-1 and XF-R 100-1. The near-field probe is small and handy. It has a current attenuating sheath and, therefore, is electrically shielded. It can be connected to a spectrum analyzer or an oscilloscope with a 50  $\Omega$  input. The H-field probe has an internal terminating resistance.

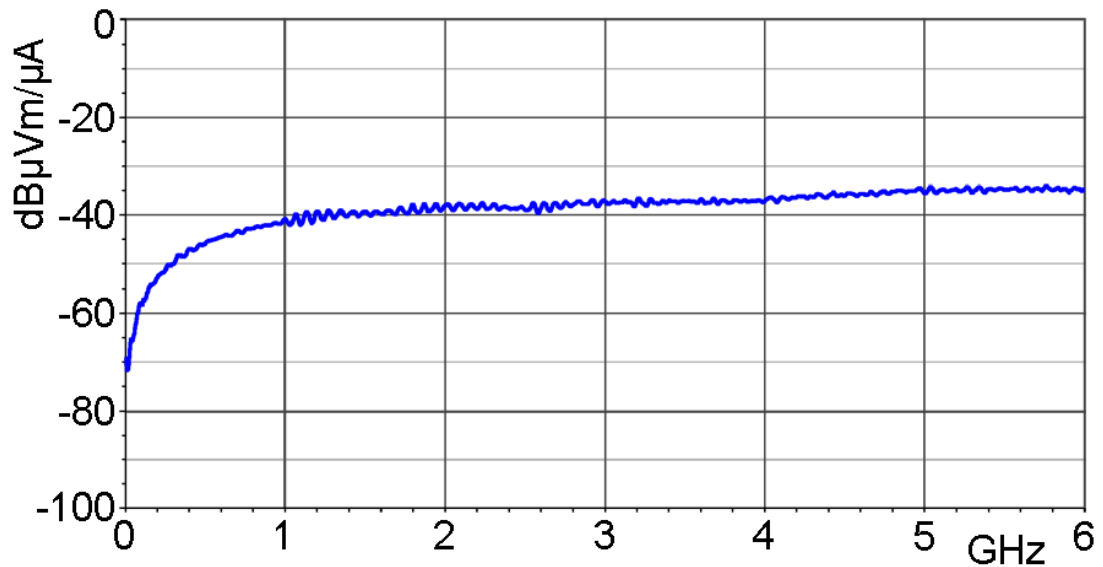
## Technical parameters

Frequency range	30 MHz ... 6 GHz
Resolution	$\approx 1$ mm
Probe head dimensions	$\varnothing \approx 3$ mm
Connector - output	SMA, female, jack
Weight	15 g

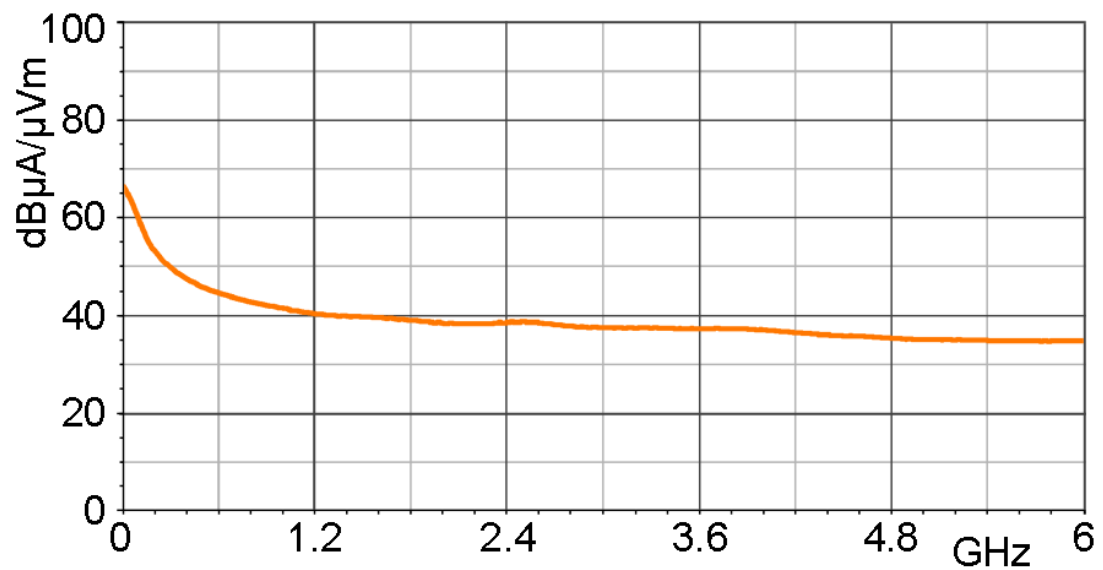
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Frequency response [dB $\mu$ V] / [dB $\mu$ A/m]



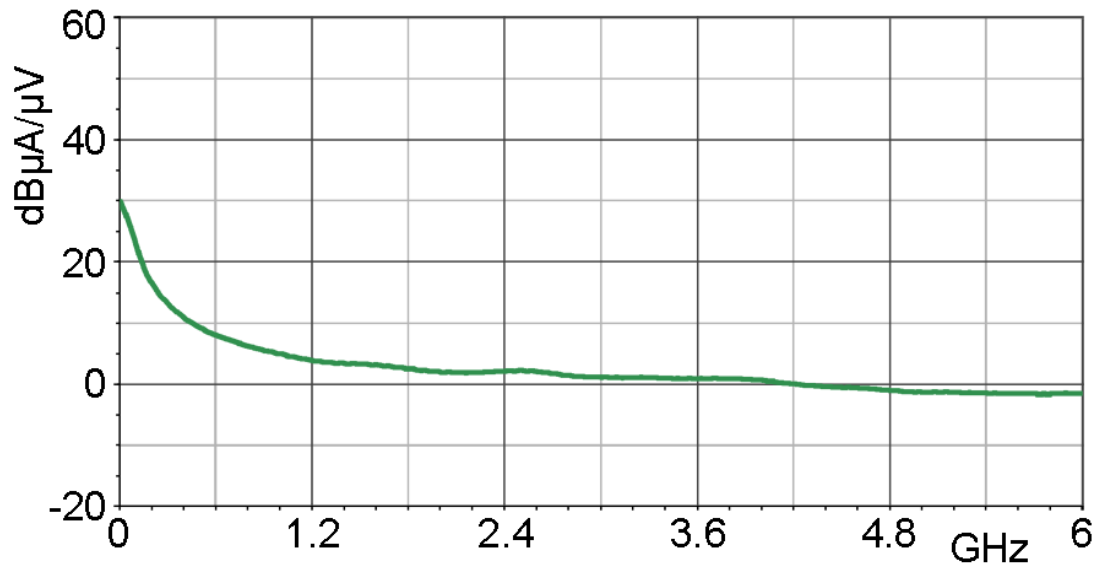
H-field correction curve [dB $\mu$ A/m] / [dB $\mu$ V]



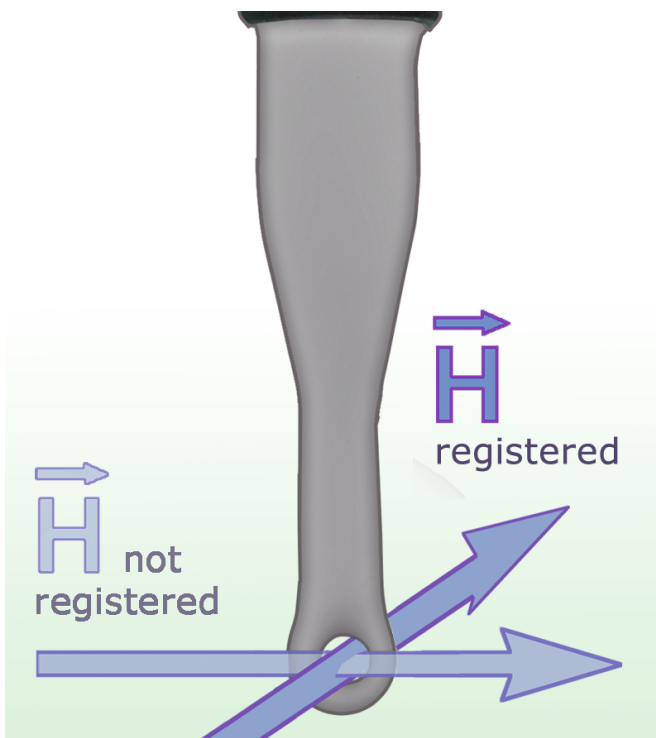
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Current correction curve [dB $\mu$ A] / [dB $\mu$ V]



Measuring principles



# XF-R 3-1

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Probe head

